













Weebit Nano AT A GLANCE

Listed on the ASX in August 2016

Targeting the storage market which is estimated at > USD\$40B

R&D and HQ in Israel, R&D partnership with CEA-Leti, France

Business & Tech partners – CEA-Leti France & Rice University, USA

Developing next-gen solution based on Silicon Oxide (SiOx) ReRAM

Patents Registered in the USA



KEY INVESTMENT HIGHLIGHTS



MASSIVE STORAGE DEMAND

Exponential increase in demand for memory storage



EXCELLENT DEVELOPMENT RESULTS

Scaled devices with a memory array significantly faster than Flash memory imminent



KEY DEVELOPMENT PARTNERSHIP

CEA-Leti, world-class research institution



MARKET DRIVERS

Content explosion and Artificial Intelligence (AI) are creating new opportunities for memory technologies (e.g. ReRAM)



ON TRACK

Working 40nm cells achieved before year end of 2017, on track for 1Mbit by mid 2018



ADDRESSABLE MARKET

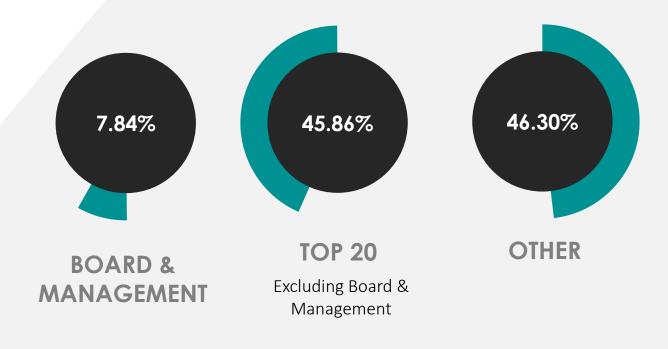
> USD\$40B+



SHARE INFORMATION

CAPITAL STRUCTURE

SHAREHOLDING BREAKDOWN





^{*}As of 27 Nov 2017

^{**}Including Options subject to approval at AGM and existing Options & Performance Shares

LEADERSHIP TEAM



Scientist of the Year 2013 R&D magazine

Inducted to the National Academy of inventors

Feynman prize in Nano science



Ex-Intel EVP IEEE Fellow

Has led intel into the Data Center

Brought to Market: Centrino™ mobile technology



Extensive management and sales experience

37 years in the semiconductor domain

Enabled Verisity and Jasper acquisitions



Two decades in Semiconductors engineering

45nm NOR Flash Technology Development at Micron

Was part of Automotive division at Intel

Confidential

THE NEW CEO

- 37 years in the semiconductor space
 - 15 years in engineering/engineering management
 - 22 years in CEO and VP Sales roles
- Verisity SVP WW Sales
 - \$315M acquisition by Cadence
- Jasper VP WW Sales
 - \$170M acquisition by Cadence
- Packetlight CEO
- EDAcon Partners







WEEBIT ReRAM TECHNOLOGY

Designed for next generation technology

ENERGY EFFICIENCY

Ultra Low Power

SPEED – READ AND WRITE

Significantly faster than Flash

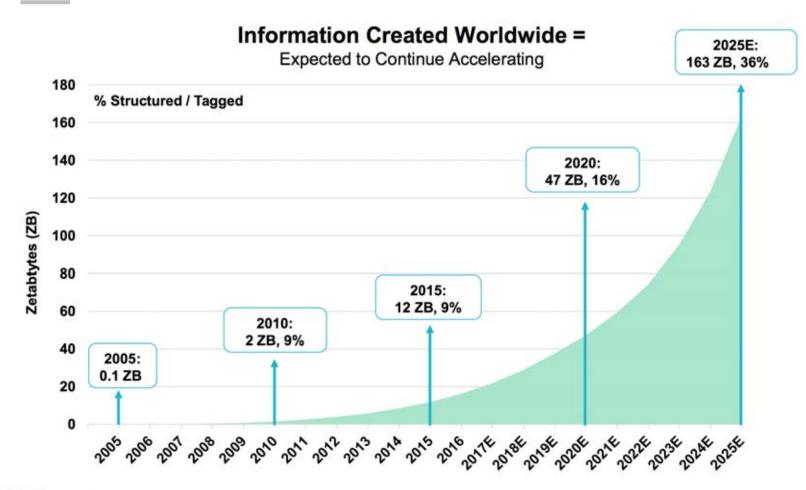
INTEGRATION

Bringing the memory closer to the processor

LOW COST / NO SPECIAL MANFACTURING TECHNOLOGY & NO RETOOLING

Manufacturability - minimum added process steps and cost

DATA EXPLOSION IS COMING



Cognitive computing and artificial intelligence will be used to analyze much of this data"

Marc Durcan
Micron CEO Micron Feb 2017

"We live in a new data

and the network that

connects them will

generate huge amounts of

data. Autonomous vehicles

generate lots of data. The

Internet of Things will also

be a big source of data.

economy that will



Source: IDC DataAge 2025 Study, sponsored by Seagate (3/17) Note: 1 petabyte = 1MM gigabytes, 1 zeta byte = 1MM petabytes



IMAGE RECOGNITION PERSONAL ASSISTANCE

INTELLIGENT MACHINES

Becoming part of our everyday lives



WEEBIT SOLUTIONS FOR THE INDUSTRY

Building smaller cell is better/cheaper

MORE INFORMATION STORED IN A PIECE OF SILICON WITH A FASTER WRITE AND READ

SILICON OXIDE

Weebit NANO NEXT-GEN MEMORY SOLUTION

- ✓ **Fab Friendly** 50 year process & manufacturing experience
- ✓ **Compatibility** well integrated with existing proven processes

MANUFACTURABLE ANYWHERE

- ✓ Any Fab no need for specialised foundry
- ✓ Any Tool no need for special tool
- ✓ Any process no need for special process



Not Used in Semiconductor Fabs

Used in Semiconductor Fabs

Shortest time to market, cheaper, Faster



RERAM COMPETITIVE LANDSCAPE









Market Capitalisation (USD)	\$50M	\$33M	\$250M (E)	\$180M
Memory Capacity	40nm cells achieved Mb Array by mid-2018	Start work on Mb Array	8Mb Array	512Kb
Dimension	40nm	40nm	40nm	130nm
 Development time	<2 years*	7 years	7 years	>10 years



COMPETITIVE ADVANTAGE









Materials	Silicon Oxide	Pr, Ca, Mn	Silver	Tellurium
Manufacturability	Production ready materials	Difficult to run in a production Fab	Difficult to run in a production Fab	Difficult to run in a production Fab
Speed	Fast RD & WR	Fast RD no data on WR	Fast RD & WR	Fast RD & WR
Retention	10Y > room temp	No data	10Y @ 85 °C	40Y @ 125 °C
Endurance	10 ⁵ *	10 ³	10 ⁶	10 ⁵
Production cost	Most cost effective process * moving to 106	Higher Cost of manufacturing	Higher Cost of manufacturing	Higher Cost of manufacturing
Based on public information		Confidential		Weebitnano The Emerging Memory





FROM PROTOTYPES TO **PRODUCTION**

Proven international track record in moving from R&D to production



MEMORY EXPERTISE

Over 10 years of experience in memory technology development



NANOTECHNOLOGY SPECIALIST

State of the art industrial tools



MANUFACTURING ALLIANCES

Over 330 industrial partners



INNOVATION HUB

60+ start-ups in semiconductor, architectures or software



Working on 40nm SiOx development since September 2016





CUSTOMERS

Intel, ST Microelectronics, Globalfoundries





Confidential

OPENED FRENCH SUBSIDIARY

- Enhances the cooperation with Leti
- Weebit will be eligible for French R&D benefits and tax refunds
- Base for our French employees





EXPECTATIONS MET

Every committed milestone met

ON TRACK

to reach 40nm

Mbit array

by mid-2018



OCT 2017

300nm 4Kbit Array with strong Endurance and retention results

MAY 2017

Miniaturisation started

MARCH 2017

Electrical results validation

NOVEMBER 2016

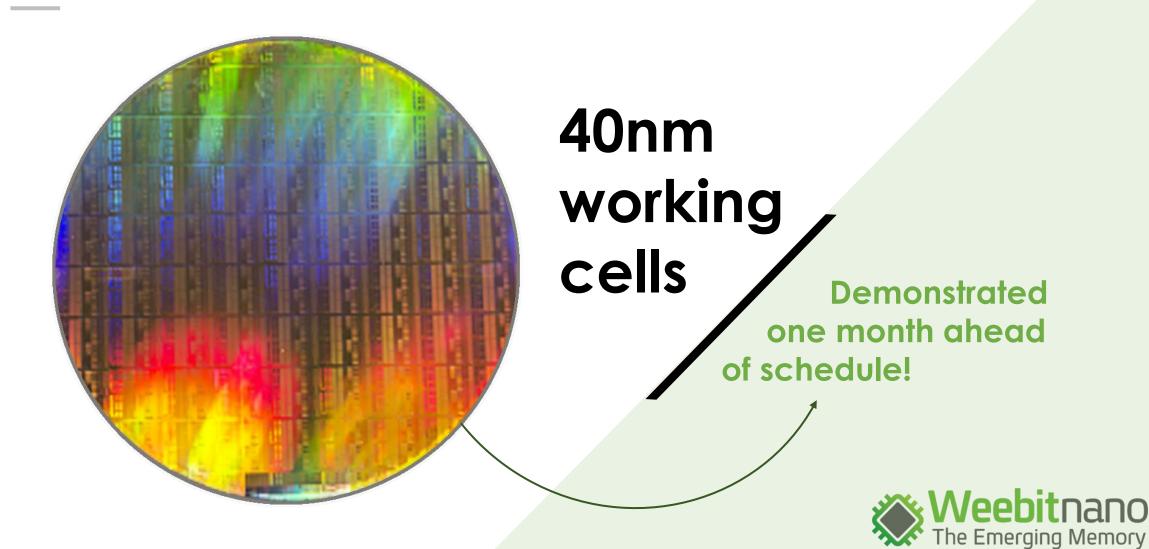
Successful Technology transfer to Leti

SEPT 2016

Development kicked off at Leti



EXPECTATIONS MET



2018 PLANS

TECHNICAL

- Develop a 40nm Mbit array by mid-2018
- Improved Endurance and Retention to meet industry standards by end 2018
- Define a plan and be on the path to develop 2xnm technology

BUSINESS

Sign first cooperation agreement with a key industry player



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